

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A device, comprising:

a waveguide core having a bottom surface and a top surface that defines a beveled mirror,
the beveled mirror confining, within the waveguide core, reflections of a mode transmitted along
the waveguide core an angle;

a cladding layer adjacent to the bottom surface, the cladding layer having a thickness
equal to or greater than an evanescent tail of a the mode to be transmitted along the waveguide
core;

a detector layer; and

an attenuating layer coupled to the bottom surface of the waveguide core and positioned
on top of the detector layer;

wherein the beveled mirror directs the mode is transmitted along from within the
waveguide core to the attenuating layer, the mode traveling through the attenuating layer and
into the detector layer.

2. (Currently Amended) The device of claim 1, wherein the beveled mirror is at an angle
relative to the waveguide core that is at least equal to an angle of total internal reflection of the
waveguide core.

3. (Canceled)

4. (Previously Presented) The device of claim 1, wherein the detector layer comprises a base of a phototransistor.

5. (Canceled)

6. (Currently Amended) The device of claim 1 5, wherein the waveguide core is disposed over a substrate and the beveled mirror directs the mode, propagated through the waveguide core, through the detector layer into the substrate.

7. (Previously Presented) The device of claim 1, wherein the detector layer comprises an intrinsic layer region of a photodiode having an n-type region and a p-type region.

8. (Currently Amended)

9. (Currently Amended) The device of claim 7 8, wherein the waveguide core is disposed over a substrate and the beveled mirror directs the mode, propagated through the waveguide core, through the detector layer into the substrate.

10 to 30. (Canceled)

31. (Currently Amended) A device, comprising:

a waveguide core having a bottom surface;

a cladding layer adjacent to the bottom surface, the cladding layer having a thickness equal to or greater than an evanescent tail of a mode ~~to be~~ transmitted along the waveguide core;

a detector layer; and

an attenuating layer coupled to the bottom surface of the waveguide core and positioned on top of the detector layer; and

a beveled mirror disposed on the waveguide core, the beveled mirror confining reflections of the mode within the waveguide core, the beveled mirror directing the mode from within the waveguide core to the attenuating layer.

32. (Previously Presented) The device of claim 31, wherein the waveguide core has a top surface that defines an angle, the angle being at least equal to an angle of total internal reflection of the waveguide core.

33. (Currently Amended) The device of claim 31, wherein the ~~waveguide core defines a beveled mirror is disposed at the angle.~~

34. (Previously Presented) The device of claim 31, wherein the detector layer comprises a base of a phototransistor.

35. (Canceled)

36. (Currently Amended) The device of claim 31 35, wherein the waveguide core is disposed over a substrate and the beveled mirror directs the mode propagated through the waveguide core and through the detector layer into the substrate.

37. (Previously Presented) The device of claim 31, wherein the detector layer comprises an intrinsic layer region of a photodiode having an n-type region-and a p-type region.

38. (Canceled)

39. (Currently Amended) The device of claim 37 38, wherein the waveguide core is disposed over a substrate and the beveled mirror directs the mode propagated through the waveguide core and through the detector layer into the substrate.

40. (Currently Amended) A device, comprising:

a waveguide core having a bottom surface, the waveguide core for transmitting a mode;
a cladding layer adjacent to the bottom surface;

a detector layer; and
an attenuating layer coupled to the bottom surface of the waveguide core and positioned
on top of the detector layer; and
a beveled mirror disposed on the waveguide core, the beveled mirror confining
reflections of the mode within the waveguide core, the beveled mirror directing the mode from
within the waveguide core to the attenuating layer, the mode traveling wherein the mode is
transmitted along the waveguide core through the attenuating layer into the detector layer.

41. (Previously Presented) The device of claim 40, wherein the waveguide core has a
top surface that defines an angle, the angle being at least equal to an angle of total internal
reflection of the waveguide core.

42. (Currently Amended) The device of claim 40, wherein the ~~waveguide core defines a~~
beveled mirror is disposed at the angle.

43. (Previously Presented) The device of claim 40, wherein the detector layer comprises
a base of a phototransistor.

44. (Canceled)

45. (Currently Amended) The device of claim 40 [[44]], wherein the waveguide core is disposed over a substrate and the beveled mirror directs a mode propagated through the waveguide core through the detector layer into the substrate.

46. (Previously Presented) The device of claim 40, wherein the detector layer comprises an intrinsic layer region of a photodiode having an n-type region and a p-type region.

47. (Canceled)

48. (Currently Amended) The device of claim 46 47, wherein the waveguide core is disposed over a substrate and the beveled mirror directs a mode, propagated through the waveguide core, through the detector layer into the substrate.

49. (Previously Presented) The device of claim 40, wherein the cladding layer has a thickness equal to or greater than an evanescent tail of a mode to be transmitted along the waveguide core.

50. (Previously Presented) The device of claim 49, wherein the mode is transmitted along the waveguide core through the attenuating layer into the detector layer.